

| Application Serial No |
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| Filing Date August 31, 2000 |
| Inventor Keiji Jono et al. |
| Assignee KMT Semiconductor, LTD |
| Group Art Unit |
| Examiner Quang D. Vu |
| Attorney's Docket No KM1-001 |
| Title: Methods of Forming an Isolation Trench in a Semiconductor, Methods of |
| Forming an Isolation Trench in a Surface of a Silicon Wafer, Methods of |
| Forming an Isolation Trench-Isolated Transistor, Trench-Isolated Transistor, |
| Trench Isolation Structures Formed in a Semiconductor, Memory Cells and |
| DRAMS |

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References - See Attached Form PTO-1449

The Examiner's attention is directed to the references which are listed on the attached Form PTO-1449, copies of which are attached. No admission is made regarding whether all the submitted references are prior art.

Citation of the referenced art is respectfully requested.

Respectfully submitted,

Dated: $3 - (9 - 9)^3$

D. Brent Kenady

Reg. No. 40,045

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| | U.S. PATENT DOCUMENTS | | | | | | | | | | |
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| *Examiner Initial | | Document Number | Date | Name | | Class | Subclass | Filing If Appro | | | |
| | AA | 6,034.409 | 03/07/2000 | Sakai et al. | | | | | | | |
| | AB | 6,171,924 B1 | 01/09/2001 | Wang et al. | | | | | | | |
| | AC | 6.154,417 | 11/28/2000 | Kim | | | | | | | |
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE.

Filing Date August 31, 2000 Inventor Keiji Jono et al. Assignee KMT Semiconductor, LTD and Micron Technology, Inc. Examiner Quang D. Vu Title: Methods of Forming an Isolation Trench in a Semiconductor, Methods of Forming an Isolation Trench in a Surface of a Silicon Wafer, Methods of Forming an Isolation Trench-Isolated Transistor, Trench-Isolated Transistor, Trench Isolation Structures Formed in a Semiconductor, Memory Cells and **DRAMS**

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References –See Attached Form PTO-1449

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Citation of the referenced art is respectfully requested.

Respectfully submitted,

TECHNOLOGY CENTER 2800

Dated: 2-2-04

By:

D. Brent Kenady

Reg. No. 40,045

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| U.S. PATENT DOCUMENTS | | | | | | | | | | | |
| *Examiner Initial | | Document Number | Date | Name | | Class 5 | Subclass | Filing Date If Appropriate | | | |
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| | AP | OTHER REF | ERENCES (ir | ncluding Author, Title, D | ate, Perti | nent Pages, Etc.) | | | | | |
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| *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | | | | | | | | | | | |